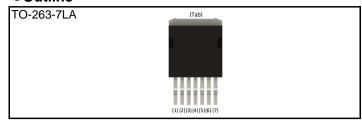
Datasheet



N-channel SiC power MOSFET

V _{DSS}	1200V
R _{DS(on)} (Typ.)	160mΩ
_D *1	17A
P_D	100W

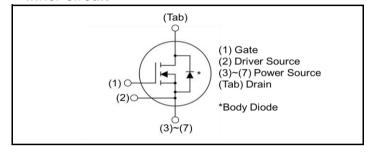
Outline



Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Type	Tape width (mm)	24
Type	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	SCT3160KWA

● **Absolute maximum ratings** (T_{vi} = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DSS}	1200	V
Continuous Drain current	T _c = 25°C	I _D *1	17	А
Continuous Diam Current	T _c = 100°C	I _D *1	12	Α
Pulsed Drain current (T _c = 25°C)		I _{D,pulse} ^{*2} 42		А
Gate - Source voltage (DC)		V_{GSS}	-4 to +22	V
Gate - Source surge voltage (t _{surge} < 300ns)		V _{GSS_surge} *4	-4 to +26	V
Recommended drive voltage		V _{GS_op} *5	0 / +18	V
Virtual Junction temperature		T_{vj}	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values		Unit
Parameter	Parameter Symbol	Conditions	Min.	Тур.	Max.	Offit
		$V_{GS} = 0V$, $I_D = 1mA$				
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$T_{vj} = 25^{\circ}C$	1200	-	-	V
renage		T _{vj} = -55°C	1200	-	-	
		$V_{GS} = 0V, V_{DS} = 1200V$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	10	μΑ
Diam current		T _{vj} = 150°C	-	2	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, \ V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -4V$, $V_{DS} = 0V$	-	ı	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V, I_D = 2.5 mA$	2.7	-	5.6	V
		$V_{GS} = 18V, I_D = 5A$				
Static Drain - Source on - state resistance	R _{DS(on)} *6	T _{vj} = 25°C	-	160	208	mΩ
		T _{vj} = 150°C	-	272	-	
Gate input resistance	R_G	f = 1MHz, open drain	-	18	-	Ω

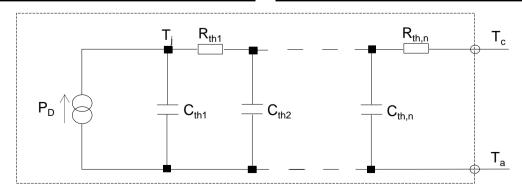
●Thermal resistance

Parameter	Symbol	Values			Unit
Farameter		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-	1.17	1.50	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.95×10 ⁻¹	
R _{th2}	3.47×10 ⁻¹	K/W
R _{th3}	5.60×10 ⁻¹	

Symbol	Value	Unit
C _{th1}	1.38×10 ⁻³	
C_{th2}	1.40×10 ⁻²	Ws/K
C _{th3}	8.68×10 ⁻³	



ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

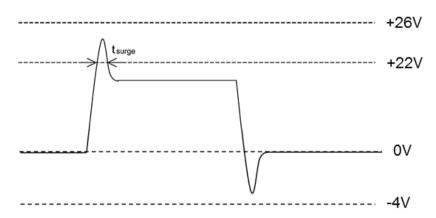
Doromotor	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g _{fs} *6	$V_{DS} = 10V, I_{D} = 5A$	-	2.5	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	398	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	41	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	18	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 600V	-	45	-	pF
Total Gate charge	Qg *6	$V_{DS} = 600V$ $I_{D} = 5A$	-	42	ı	
Gate - Source charge	Q _{gs} *6	$V_{GS} = 18V$	-	10	-	nC
Gate - Drain charge	Q _{gd} *6	See Fig. 1-1.	-	22	-	
Turn - on delay time	t _{d(on)} *6	$V_{DS} = 600V$ $I_{D} = 5A$	-	3	-	
Rise time	t _r *6	$V_{GS} = 0V/+18V$	-	9	-	no
Turn - off delay time	t _{d(off)} *6	$R_G = 0\Omega$, L = 750µH E_{on} includes diode	-	14	-	ns
Fall time	t _f *6	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	-	9	-	
Turn - on switching loss	E _{on} *6	See Fig. 2-1, 2-2, 2-3.	-	75	-	1
Turn - off switching loss	E _{off} *6		-	7	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values	Unit	
- raiametei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Body diode continuous, forward current	I _S *1	T _c = 25°C	-	-	17	А
Body diode direct current, pulsed	I _{SM} *1,3	11 _c = 25 0	ı	ı	42	А
Forward voltage	V _{SD} *6	$V_{GS} = 0V, I_S = 5A$	ı	3.2	ı	V
Reverse recovery time	t _{rr} *6	$I_F = 5A$ $V_R = 600V$	ı	11	ı	ns
Reverse recovery charge	Q _{rr} *6	di/dt = 2500A/µs	-	108	-	nC
Peak reverse recovery current	I _{rrm} *6	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	20	-	А

^{*1} Limited by maximum T_{vj} and for Max. R_{thJC} .

*4 Example of acceptable V_{GS} waveform



Please note especially when using driver source that $V_{\text{GSS_surge}}$ must be in the range of absolute maximum rating.

*5 Please be advised not to use SiC-MOSFETs with V_{GS} below 13V as doing so may cause thermal runaway.

*6 Pulsed

^{*2} Pulse width and duty cycle are limited by $T_{\nu_{j,max}}$.

^{*3} PW \leq 10 μ s, Duty cycle \leq 1%

Fig.1 Power Dissipation Derating Curve

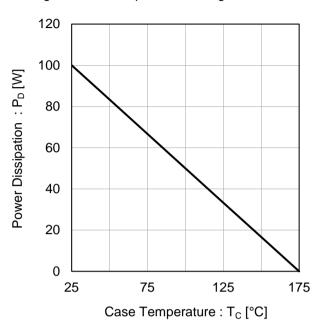


Fig.2 Maximum Safe Operating Area

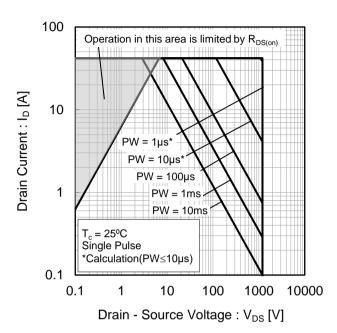


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width

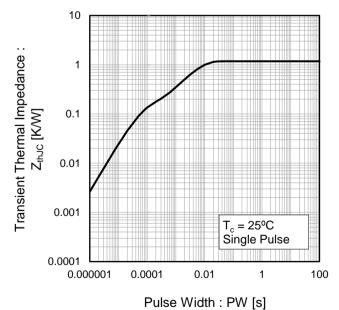


Fig.4 Typical Output Characteristics(I)

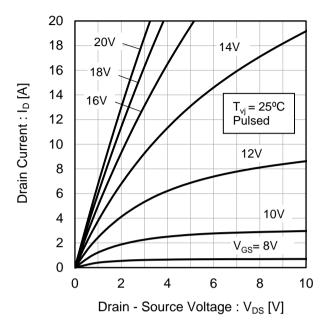


Fig.5 Typical Output Characteristics(II)

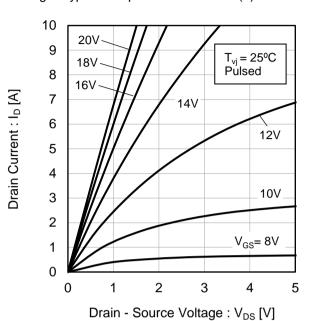
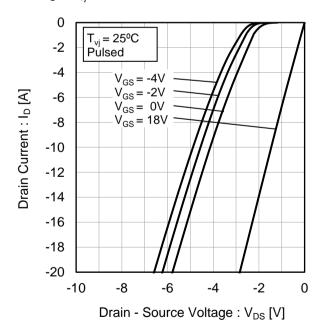
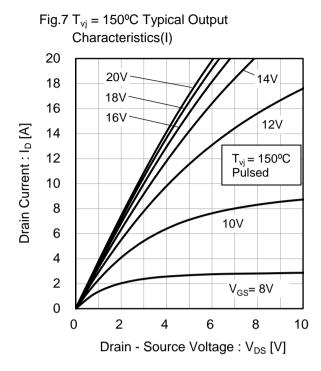


Fig.6 T_{vj} = 25°C 3rd Quadrant Characteristics



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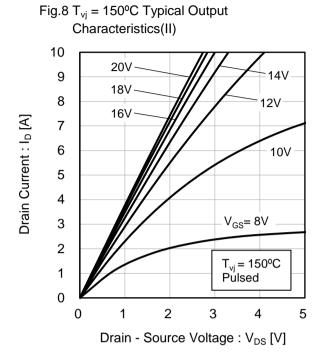


Fig.9 T_{vj} = 150°C 3rd Quadrant Characteristics

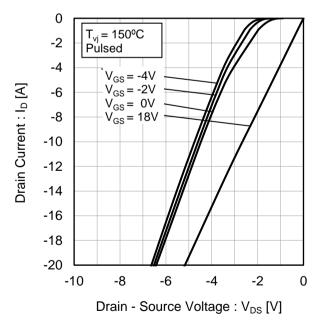


Fig.10 Body Diode Forward Voltage vs. Gate - Source Voltage

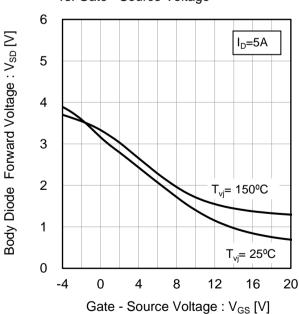


Fig.11 Typical Transfer Characteristics (I)

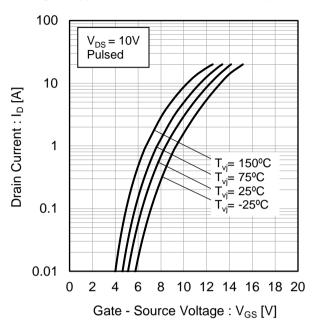


Fig.12 Typical Transfer Characteristics (II)

Datasheet

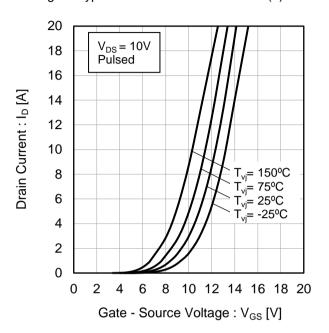


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

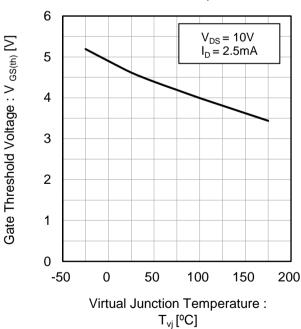
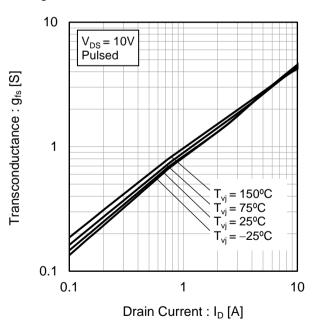
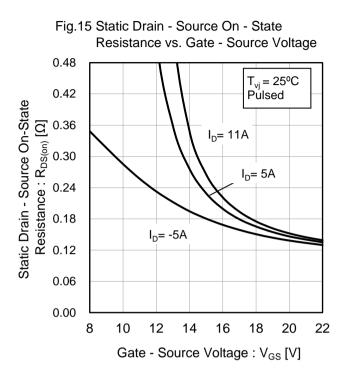
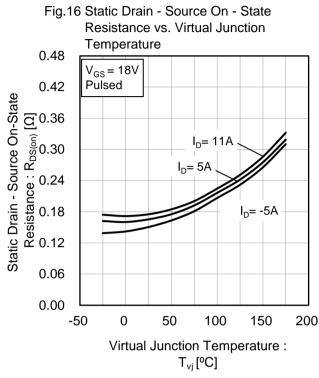


Fig.14 Transconductance vs. Drain Current







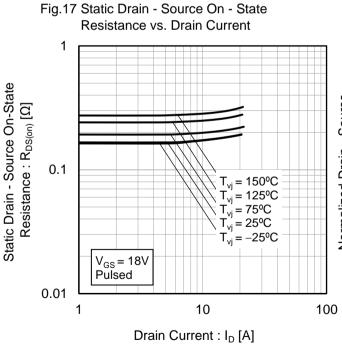


Fig.18 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction Temperature 1.04 $V_{GS} = 18V$ Pulsed 1.03 Normalized Drain - Source **Breakdown Voltage** 1.02 1.01 1.00 0.99 0.98 -50 0 50 100 150 200 Virtual Junction Temperature: T_{vi} [°C]

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Fig.19 Typical Capacitance vs. Drain - Source Voltage 10000 1000 Ciss Capacitance: C [pF] 100 $\mathsf{C}_{\mathsf{rss}}$ 10 $T_{vj} = 25^{\circ}C$ f = 1MHz $V_{GS} = 0V$ 1 1 10 100 0.1 1000 Drain - Source Voltage : V_{DS} [V]

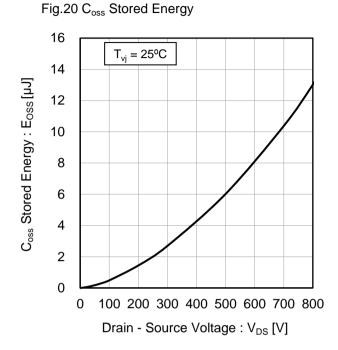
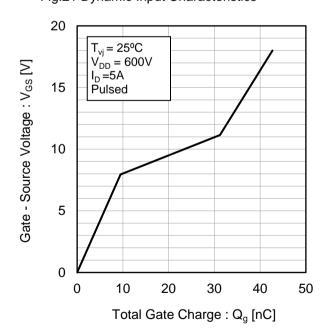


Fig.21 Dynamic Input Characteristics



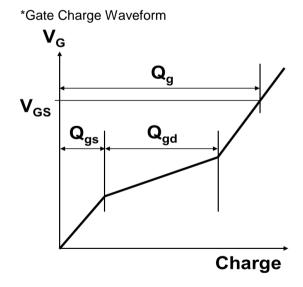


Fig.22 Typical Switching Time vs. External Gate Resistance

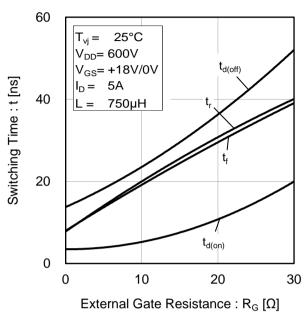


Fig.23 Typical Switching Loss vs. Drain - Source Voltage

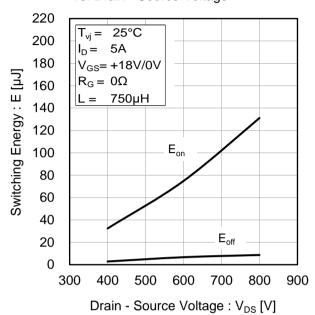


Fig.24 Typical Switching Loss vs. Drain Current

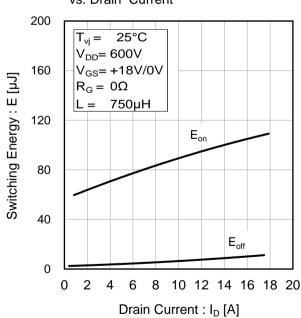
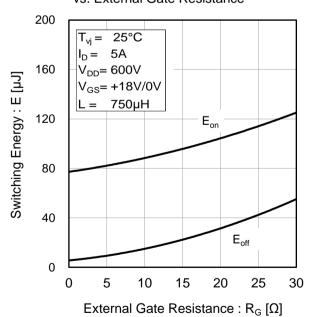


Fig.25 Typical Switching Loss vs. External Gate Resistance



Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

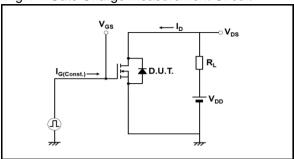


Fig.2-1 Switching Characteristics Measurement Circuit

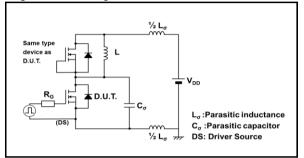


Fig.2-2 Waveforms for Switching Time

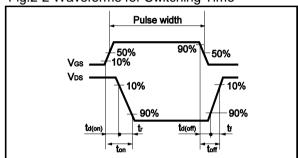


Fig.2-3 Waveforms for Switching Energy Loss

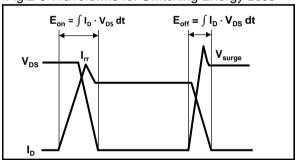


Fig.3-1 Reverse Recovery Time Measurement Circuit

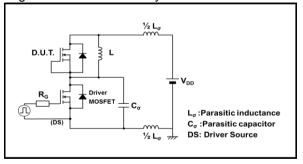
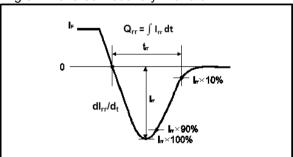
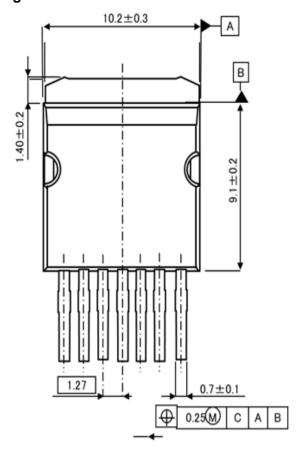
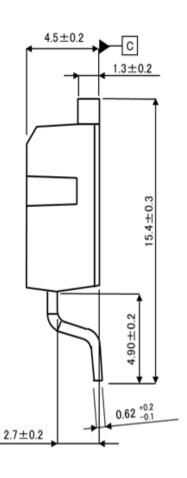


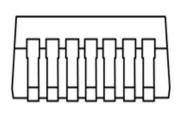
Fig.3-2 Reverse Recovery Waveform

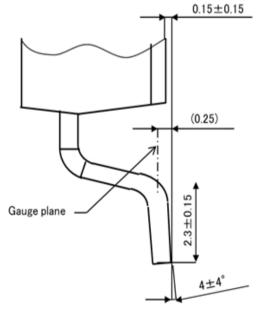


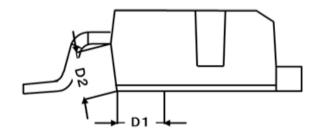
● Package Dimensions





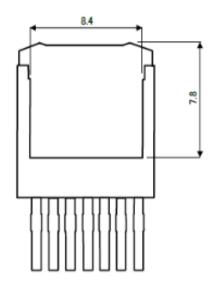




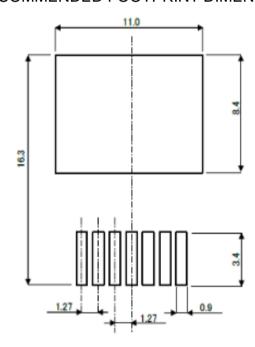


Minimum Creepage Distance = 4.7mm (D1+D2)

Unit: mm



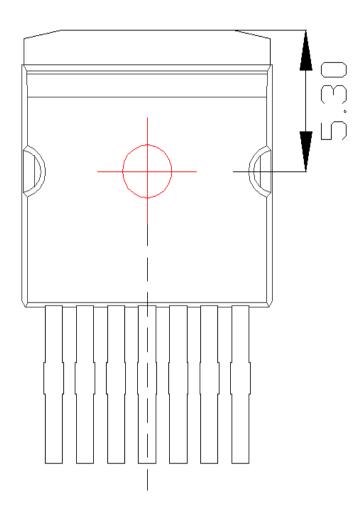
RECOMMENDED FOOTPRINT DIMENSIONS



Unit: mm

●Die Bonding Layout





- •Front view of the packaging.
- ·Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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